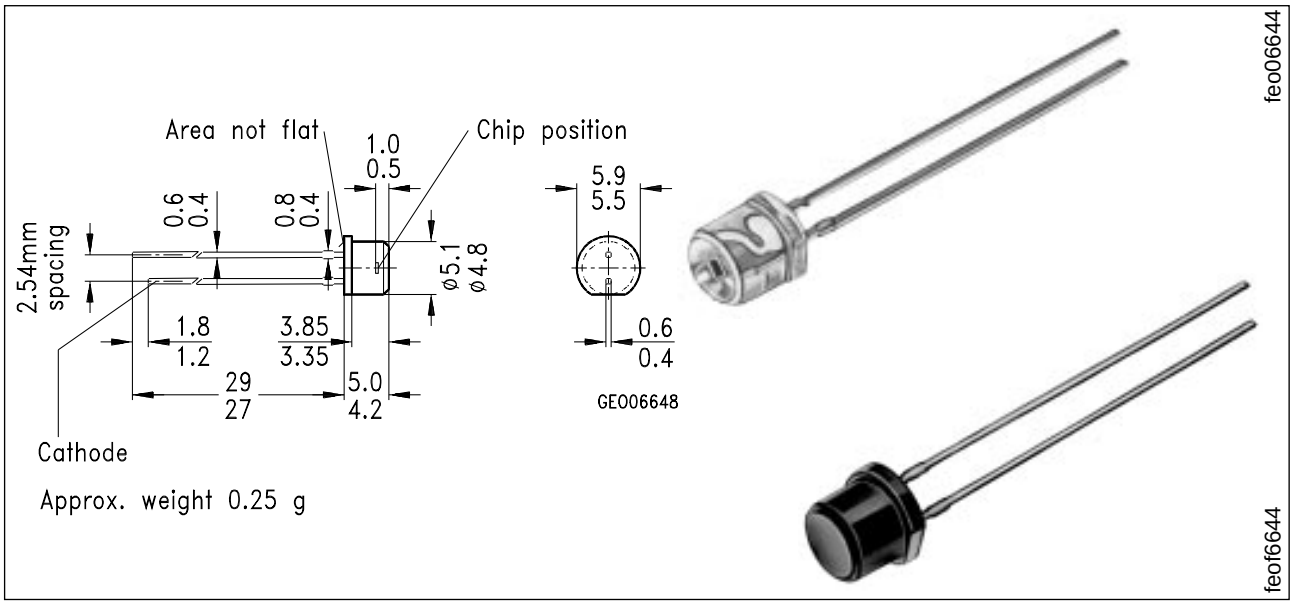
SIEMENS

Silizium-PIN-Fotodiode mit sehr kurzer Schaltzeit — SFH 203 P
Silicon PIN Photodiode with Very Short Switching Time — SFH 203 PFA



Maße in mm, wenn nicht anders angegeben/Dimensions in mm, unless otherwise specified.

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm (SFH 203 P) und bei 880 nm (SFH 203 PFA)
- Kurze Schaltzeit (typ. 5 ns)
- 5 mm-Plastikbauform im LED-Gehäuse

Anwendungen

- Industrieelektronik
- “Messen/Steuern/Regeln”
- Schnelle Lichtschranken für Gleich- und Wechsellichtbetrieb
- LWL

Features

- Especially suitable for applications from 400 nm to 1100 nm (SFH 203 P) and of 880 nm (SFH 203 PFA)
- Short switching time (typ. 5 ns)
- 5 mm LED plastic package

Applications

- Industrial electronics
- For control and drive circuits
- Photointerrupters
- Fiber optic transmission systems

Typ (*vorher) Type (*formerly)	Bestellnummer Ordering Code
SFH 203 P (*SFH 217)	Q62702-P946
SFH 203 PFA (*SFH 217 F)	Q62702-P947

Grenzwerte
Maximum Ratings

Bezeichnung **Description**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}; T_{stg}	– 55 ... + 100	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ($t \leq 3$ s)	T_S	300	°C
Sperrspannung Reverse voltage	V_R	50	V
Verlustleistung Total power dissipation	P_{tot}	100	mW

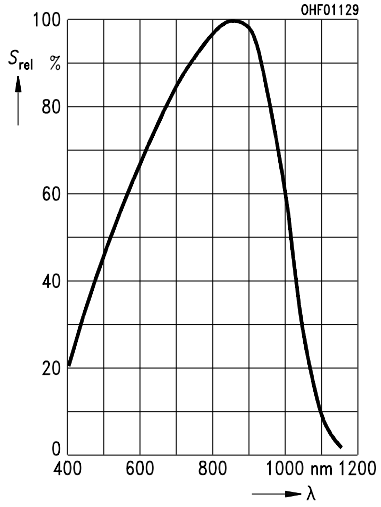
Kennwerte (T_A = 25 °C)
Characteristics

Bezeichnung **Description**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		SFH 203 P	**SFH 203 PFA**	
Fotoempfindlichkeit Spectral sensitivity V_R = 5 V, Normlicht/standard light A, T = 2856 K	S	9.5 (≥ 5)	–	nA/lx
V_R = 5 V, λ = 950 nm, E_e = 1 mW/cm^2	S	–	6.2 (≥ 3.6)	µA
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\,max}$	850	900	nm
Spektraler Bereich der Fotoempfindlichkeit S = 10 % von S_{max} Spectral range of sensitivity S = 10 % of S_{max}	λ	400 ... 1100	750 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	1	1	mm^2
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	1 × 1	1 × 1	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	0.4 ... 0.7	0.4 ... 0.7	mm

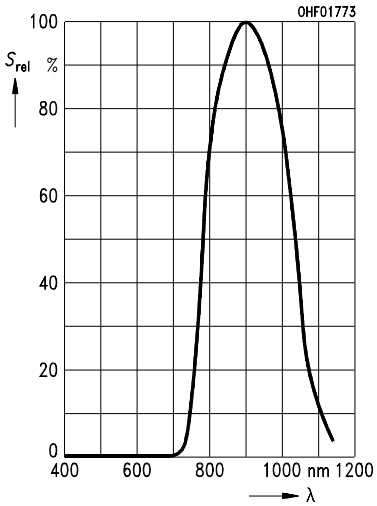
Kennwerte (T_A = 25 °C)
Characteristics (cont'd)

Bezeichnung **Description**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		SFH 203 P	**SFH 203 PFA**	
Halbwinkel Half angle	φ	± 75	± 75	Grad deg.
Dunkelstrom, V_R = 20 V Dark current	I_R	1 (≤ 10)	1 (≤ 10)	nA
Spektrale Fotoempfindlichkeit, λ = 850 nm Spectral sensitivity	S_λ	0.62	0.59	A/W
Quantenausbeute, λ = 850 nm Quantum yield	η	0.89	0.86	Electrons Photon
Leerlaufspannung Open-circuit voltage E_v = 1000 lx, Normlicht/standard light A, T = 2856 K E_e = 0.5 mW/cm², λ = 950 nm	V_O V_O	350 (≥ 300) –	– 300 (≥ 250)	mV mV
Kurzschlußstrom Short-circuit current E_v = 1000 lx, Normlicht/standard light A, T = 2856 K E_e = 0.5 mW/cm², λ = 950 nm	I_{SC} I_{SC}	9.3 –	– 3.0	µA µA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent R_L = 50 Ω; V_R = 20 V; λ = 850 nm; I_p = 800 µA	t_r, t_f	5	5	ns
Durchlaßspannung, I_F = 80 mA, E = 0 Forward voltage	V_F	1.3	1.3	V
Kapazität, V_R = 0 V, f = 1 MHz, E = 0 Capacitance	C_0	11	11	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	– 2.6	– 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC} Normlicht/standard light A λ = 950 nm	TC_I	 0.18 –	 – 0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power V_R = 20 V, λ = 850 nm	NEP	2.9×10^{-14}	2.9×10^{-14}	$\frac{W}{\sqrt{Hz}}$
Nachweisgrenze, V_R = 20 V, λ = 850 nm Detection limit	D*	3.5×10^{12}	3.5×10^{12}	$\frac{cm \cdot \sqrt{Hz}}{W}$

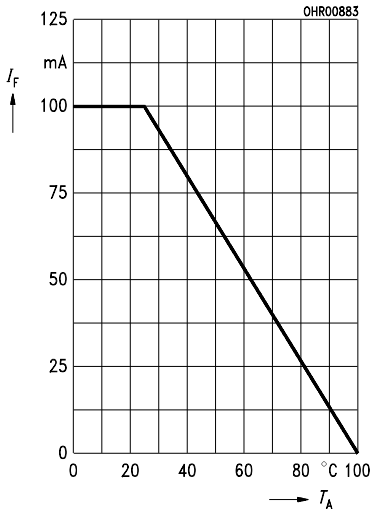
Relative spectral sensitivity SFH 203 P
$S_{rel} = f\ (\lambda)$



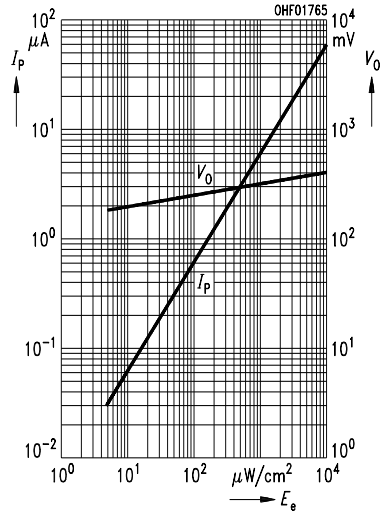
Relative spectr. sensitivity SFH 203 PFA
$S_{rel} = f\ (\lambda)$



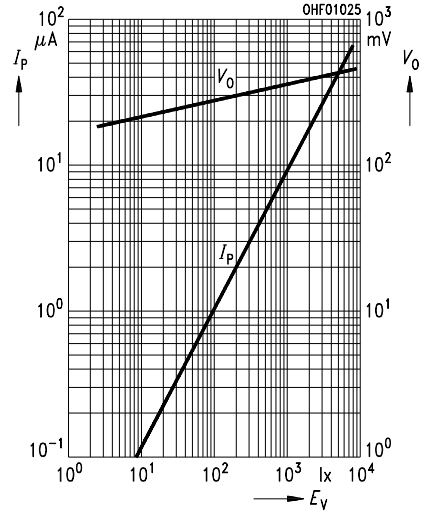
Total power dissipation
$P_{tot} = f\ (T_A)$



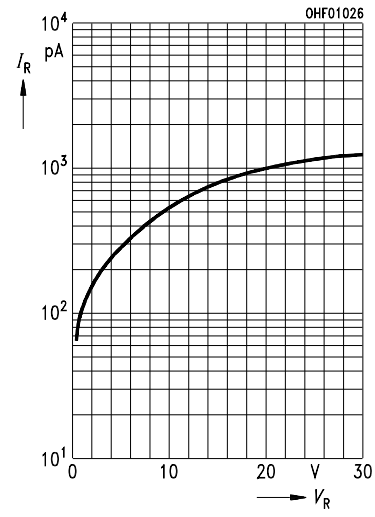
Photocurrent $I_P = f\ (E_e)$, V_R = 5 V
Open-circuit voltage $V_O = f\ (E_e)$
SFH 203 PFA



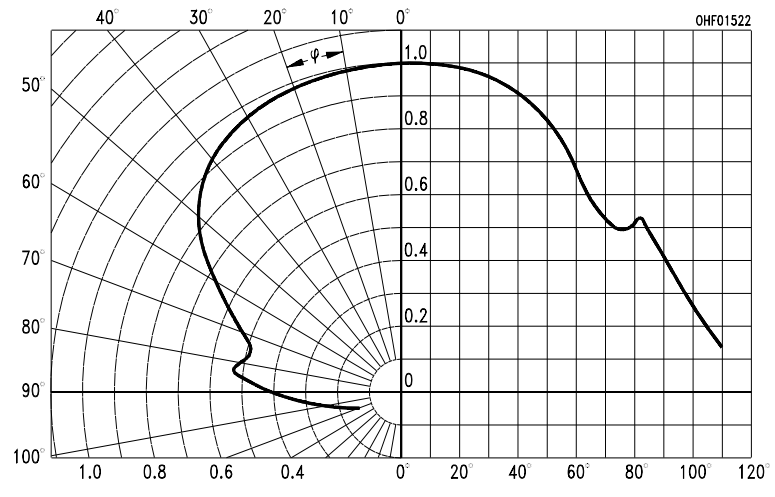
Photocurrent $I_P = f\ (E_v)$, V_R = 5 V
Open-circuit voltage $V_O = f\ (E_v)$
SFH 203 P



Dark current
$I_R = f\ (V_R)$, E = 0



Directional characteristics $S_{rel} = f\ (\varphi)$



Capacitance
$C = f\ (V_R)$, f = 1 MHz, E = 0